HUASHUO SEMICONDUCTOR

HSMA8076A

N-Ch 80V Fast Switching MOSFETs

Description

The HSMA8076A is the high cell density SGT N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous rectification applications.

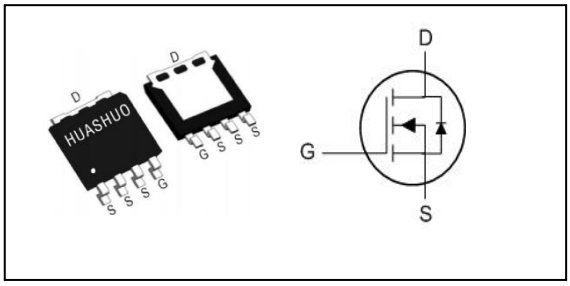
The HSMA8076A meet the RoHS and Halogen-Free compliant product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	80	V
$R_{DS(ON),typ}$	1.75	mΩ
I_D	255	A

LFPAK5X6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	255	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	155	A
I_D@T_A=25℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	35	A
I_D@T_A=100℃	Continuous Drain Current, V_{GS} @ 10V[1,6]	22	A
I_{DM}	Pulsed Drain Current[2]	630	A
EAS	Single Pulse Avalanche Energy[3]	180	mJ
I_{AS}	Avalanche Current	60	A
P_D@T_C=25℃	Total Power Dissipation[4]	245	W
P_D@T_A=25℃	Total Power Dissipation[4]	5.2	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient [1]	---	24	℃/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	---	0.51	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=30A	---	1.75	2.2	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	2	2.9	4	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=64V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=64V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	1.4	---	Ω
Qg	Total Gate Charge (10V)	V_{DS}=40V , V_{GS}=10V , I_D=30A	---	101	---	nC
Qgs	Gate-Source Charge		---	26	---	
Qgd	Gate-Drain Charge		---	27	---	
Td(on)	Turn-On Delay Time	V_{DD}=40V , V_{GS}=10V , R_G=3.3Ω, I_D=30A	---	22	---	ns
Tr	Rise Time		---	49	---	
Td(off)	Turn-Off Delay Time		---	54	---	
Tf	Fall Time		---	41	---	
Ciss	Input Capacitance	V_{DS}=40V , V_{GS}=0V , f=1MHz	---	6560	---	pF
Coss	Output Capacitance		---	1051	---	
Crss	Reverse Transfer Capacitance		---	115	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	100	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=30A , dI/dt=100A/μs , T_J=25℃	---	76	---	nS
Q_{rr}	Reverse Recovery Charge		---	173	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=60A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
6.The maximum current rating is package limited.

Typical Characteristics

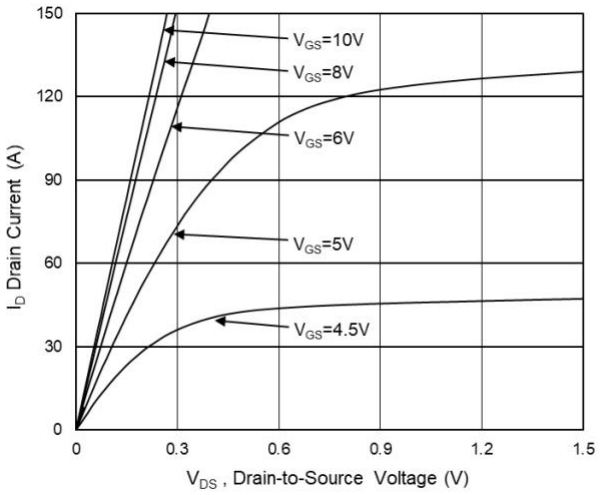


Fig.1 Typical Output Characteristics

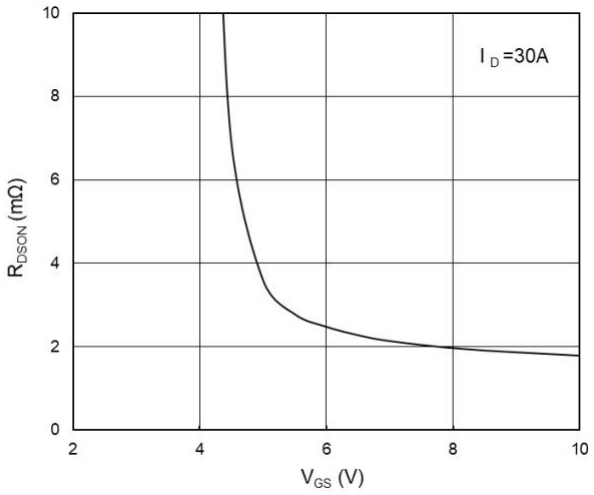


Fig.2 On-Resistance vs G-S Voltage

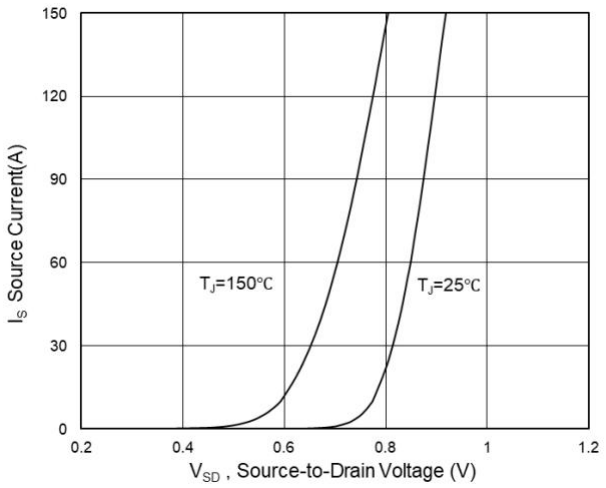


Fig.3 Source Drain Forward Characteristics

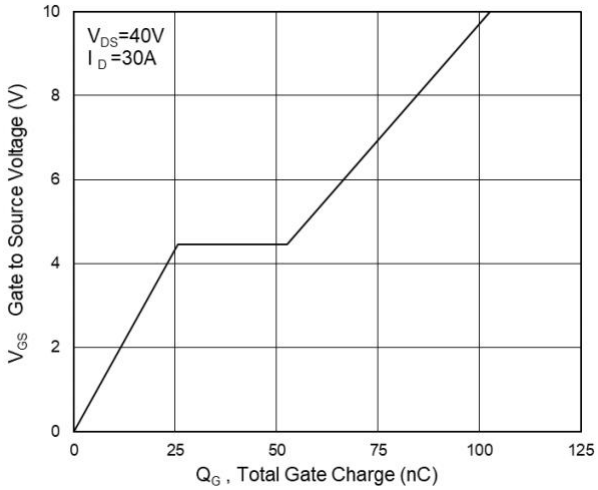


Fig.4 Gate-Charge Characteristics

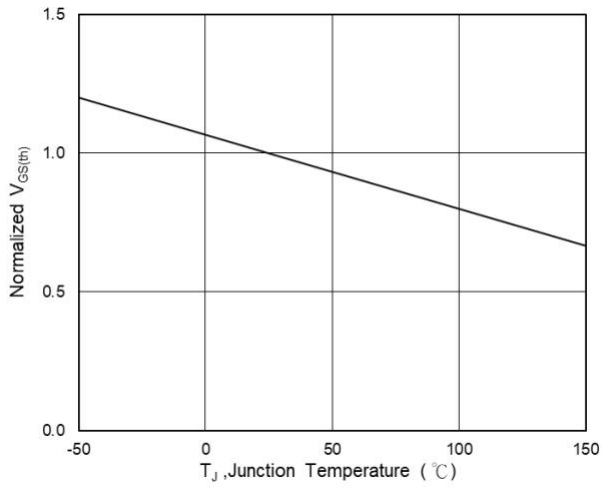


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

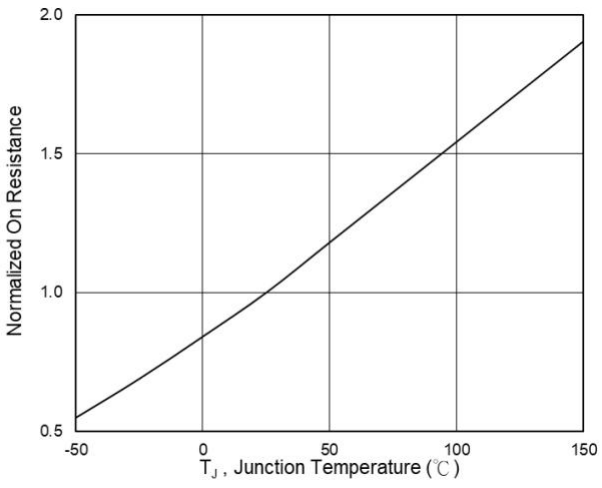


Fig.6 Normalized R_{DSON} vs. T_J

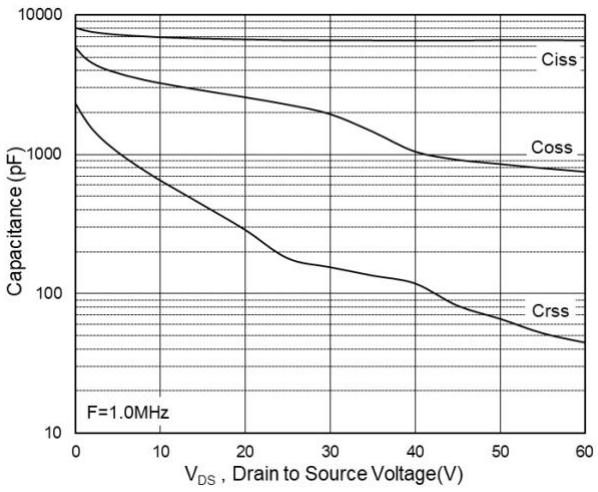


Fig.7 Capacitance

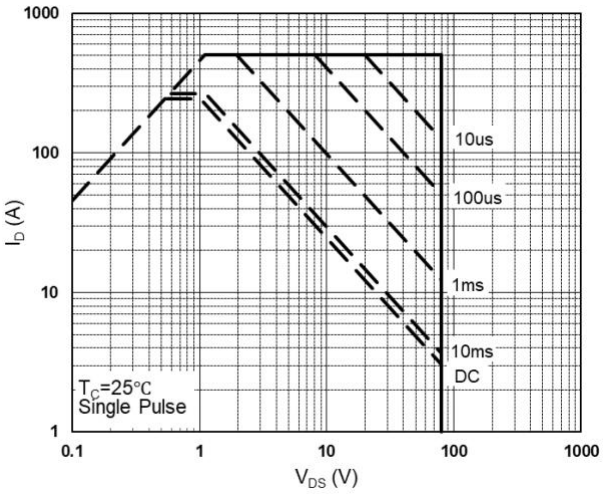


Fig.8 Safe Operating Area

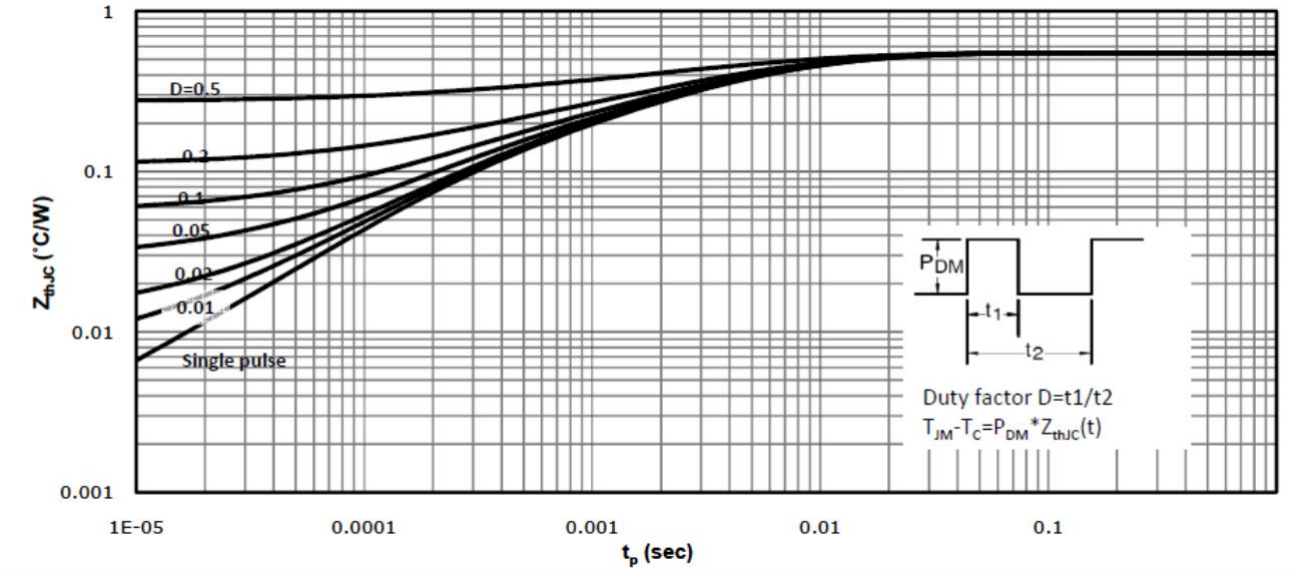


Fig.9 Normalized Maximum Transient Thermal Impedance

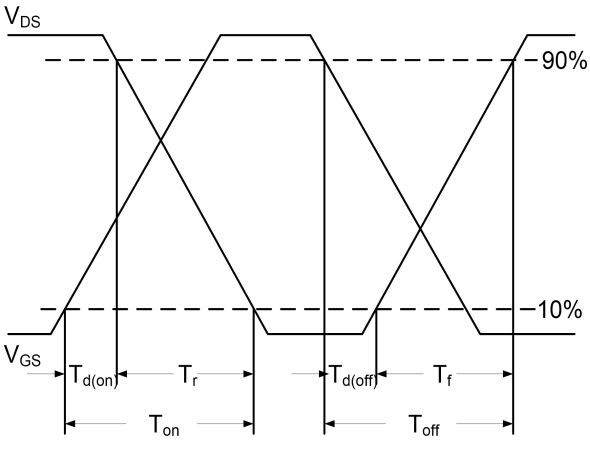


Fig.10 Switching Time Waveform

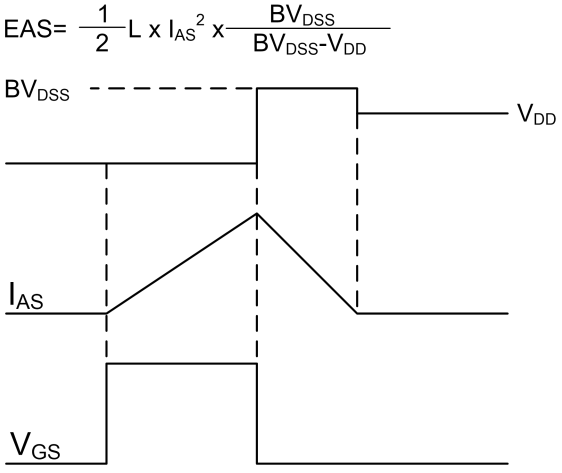


Fig.11 Unclamped Inductive Switching Waveform